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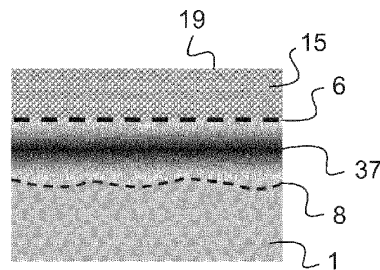
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- (54) **Title: DEEP JUNCTION ELECTRONIC DEVICE AND PROCESS FOR MANUFACTURING THEREOF**

Fig.12



- (57) **Abstract:** The invention concerns a process for manufacturing a deep junction electronic device comprising the steps of: b) Depositing a layer (5) of non monocrystalline semiconductor material on a plane surface (9) of a substrate (1) of a monocrystalline semiconductor material; c) Incorporating inactivated dopant elements prior to step b) into said substrate (1) and/or, respectively, during or after step b) into said layer (5), so as to form an inactivated doped layer (7, 27); d) Exposing, an external surface (19) of the layer (5) formed at step b) to a laser thermal anneal beam (30), so as to melt said layer (5) down to the substrate (1) and so as to activate said dopant elements incorporated at step c); e) Stopping exposure to the laser beam so as to induce epi-like crystallization of the melted layer (5), so that said substrate (1) and/or, respectively, an epi-like monocrystalline semiconductor material, comprises a layer (17, 27) of activated doped monocrystalline semiconductor material.

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